陳柏勳老師期刊論文

項次	期刊論文名稱
1	Wei-Chen Huang, Shin-Ping Huang, Po-Hsun Chen*, Min-Chen Chen,TingChang Chang*, Chih-Cheng Shih, Yi- Ting Tseng, Hao-Xuan Zheng, Yung-Fang Tan, Chung-Wei Wu, Yuh-Suan Yeh, Xiao-Hua Ma, Yue Hao, Simon M Sze (2020, Jan). Investigation of the forming process under UV illumination in HfO2-based resistance random access memory with a transparent electrode. Journal of Physics D: Applied Physics, 53(2), 025104. 本人為通訊作者
2	Po-Hsun Chen*, Huei-Jyun Shih, Philip Jwo Li (2019, Nov). Effects of varying nitride concentration in Ar:N_2 sputtering of indium-tin-oxide film for use as electrode in resistance switching device. Journal of Alloys and Compounds, 808(5), 151654. MOST 108-2218-E-012-001-MY3. 本人為第一作者、通訊作者
3	Shin-Ping Huang, Po-Hsun Chen*, Yu-Ching Tsao, Hong-Chih Chen, Yu-Zhe Zheng, Ann-Kuo Chu, Yu-Shan Shih, Yu-Xuan Wang, Chia-Chuan Wu, Yao-Kai Shih, Yu-Hua Chung, Wei-Han Chen, Terry Tai-Jui Wang, Sheng-Dong Zhang, Ting-Chang Chang* (2019, Nov). Abnormal C–V Hump Effect Induced by Hot Carriers in Gate Length-Dependent p-Type LTPS TFTs. IEEE Transactions on Electron Devices, 66(11), 4764-4767. 本人為通訊作者
4	Po Hsun Chen, Yu Ching Tsao, Yu Chieh Chien, Hsiao-Cheng Chiang, Hua-Mao Chen, Ying-Hsin Lu, Chih-Cheng Shih, Mao-Chou Tai, Guan-Fu Chen, Yu-Lin Tsai, Hui-Chun Huang, Tsung-Ming Tsai, Ting-Chang Chang (2019, Aug). A Dual Gate InGaZnO4 Based Thin Film Transistor for High Sensitivity UV Detection. Advanced Materials Technologies, 4(8), 1900106. 本人為第一作者.
5	Chun-Chu Lin*, Po-Hsun Chen*, Min-Chen Chen, Ting-Chang Chang, Chih-Yang Lin, Hao-Xuan Zheng, Chun-Kuei Chen, Wei-Chen Huang, Wen-Chung Chen, Hui-Chun Huang, Tsung-Ming Tsai, Xiao-Hua Ma, Yue Hao, Simon M. Sze (2019, Jun). Investigating Material Changes at Different Gadolinium Doping Power Levels in Indium-Tin Oxide Intended for Use as an Insulator in Resistive Switching Memory. IEEE Transactions on Electron Devices, 66(6), 2595-2599. MOST 108-2218-E-012-001-MY3. 本人為第一作者
6	Po-Hsun Chen*, Yu-Ting Su, Fu-Chen Chang (2019, Mar). Stabilizing Resistive Switching Characteristics by Inserting Indium-Tin-Oxide Layer as Oxygen Ion Reservoir in HfO2-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 66(3), 1276-1280. MOST 108-2218-E-012-001-MY3. 本人為第一作者、通訊作者
7	Chih-Yang Lin, Chih-Hung Pan, Po-Hsun Chen*, Ting-Chang Chang*, TsungMing Tsai, Chun-Kuei Chen, Yun-Hsuan Lin, Wei-Chen Huang, Chun-Chu Lin, Wen-Chung Chen (2019, Feb). Predicting voltage induced positive-feedback effect on dynamic

	reset behavior in resistance switching device. Journal of Physics D: Applied Physics, 52(9), 095108. 本人為通訊作者
8	Chih Cheng Yang*, Po Hsun Chen*, Chih-Cheng Shih, Ming-Hui Wang, Tsung Ming Tsai, Hao-Xuan Zheng, Wen-Chung Chen, Min-Chen Chen, Hui-Chun Huang, Xiao Hua Ma, Yue Hao, Jen-Wei Huang, Simon M. Sze, Ting-Chang Chang (2018, Nov). Enhancement of Surface Chemical and Physical Properties of Germanium–Sulfur Thin Film Using a Water Supplemented Carbon Dioxide Supercritical Fluid Treatment Technique. Advanced Materials Interfaces, 5(21), 1801105. 本人為第一作者